

OptiMOS 3 Power-Transistor Features N-channel, normal level

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-263
Product Type	Discrete Semiconductors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for IPB054N08N3G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

IPB054N08N3G is a power MOSFET transistor manufactured by Infineon Technologies. Here are some of its features:

Features

It has a drain-source voltage rating of 80V and a continuous drain current rating of 75A.

The device has a low on-resistance of 5.4 milliohms, which helps reduce power dissipation and improve efficiency.

It is designed for use in switching applications and features fast switching times and low gate charge.

The device has a compact TO-263-7 package with a small footprint, which makes it suitable for space-constrained applications.

Application

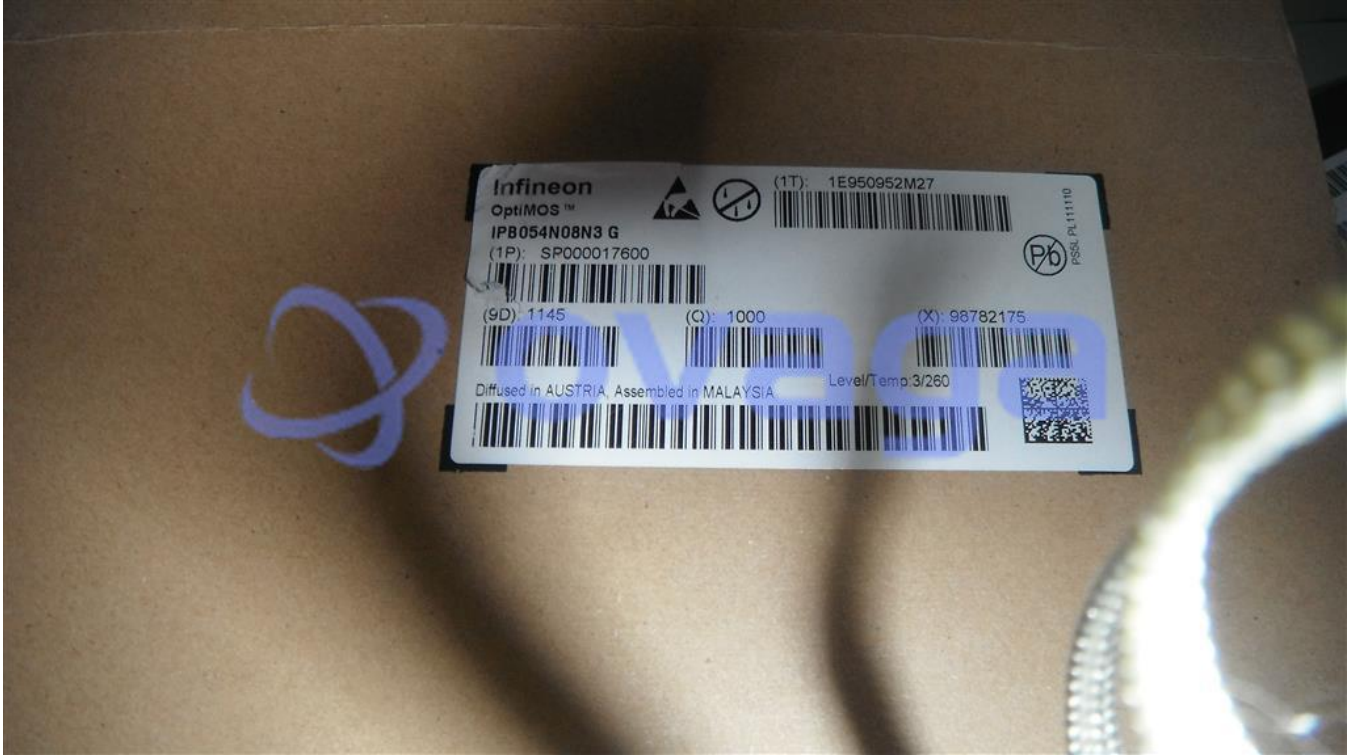
DC-DC converters

Motor control

Power supplies

Inverters

Lighting applications



Related Products



[IPA60R180C7](#)

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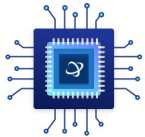
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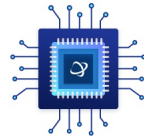
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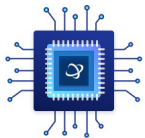
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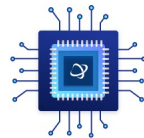
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